**Product data sheet** 

# 1. General description

PNP low  $V_{\text{CEsat}}$  transistor in a SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package.

NPN complement: PBSS8110T

### 2. Features and benefits

- Low collector-emitter saturation voltage V<sub>CEsat</sub> and corresponding low R<sub>CEsat</sub>
- High collector current capability
- · High collector current gain
- Improved efficiency due to reduced heat generation
- Qualified according to AEC-Q101 and recommended for use in automotive applications

## 3. Applications

- Major application segments
  - Automotive 42 V power
  - · Telecom infrastructure
  - Industrial
- DC/DC converters
- Peripheral drivers
  - Driver in low supply voltage applications (e.g. lamps and LEDs)
  - Inductive load driver (e.g. relays, buzzers and motors)

### 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	-100	V
I <sub>C</sub>	collector current		-	-	-1	Α
I <sub>CM</sub>	peak collector current	limited by T <sub>j(max)</sub>	-	-	-3	Α
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C$ = -1 A; $I_B$ = -100 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	170	320	mΩ



100 V, 1 A PNP low VCEsat transistor

# 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	3	_
2	E	emitter		C 
3	С	collector		В
				E sym132
			SOT23	,

## 6. Ordering information

## **Table 3. Ordering information**

Type number Package					
	Name	Description	Version		
PBSS9110T-Q	SOT23	plastic, surface-mounted package; 3 terminals; 1.9 mm pitch; 2.9 mm x 1.3 mm x 1 mm body	SOT23		

## 7. Marking

#### Table 4. Marking codes

Type number	Marking code[1]
PBSS9110T-Q	%U7

[1] % = placeholder for manufacturing site code

# 8. Limiting values

#### Table 5. Limiting values

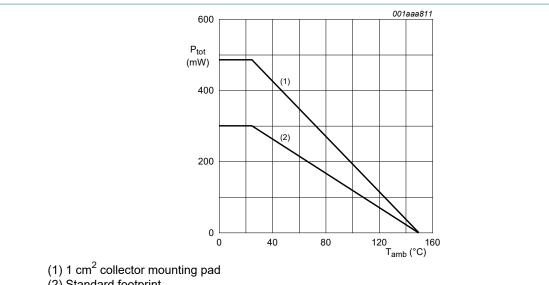
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{CBO}$	collector-base voltage	open emitter		-	-120	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-100	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	-5	V
Ic	collector current			-	-1	А
I <sub>CM</sub>	peak collector current	limited by T <sub>j(max)</sub>		-	-3	Α
I <sub>B</sub>	base current			-	-300	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	300	mW
			[2]	-	480	mW
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-65	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.

### 100 V, 1 A PNP low VCEsat transistor



(2) Standard footprint

Power derating curves Fig. 1.

## 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
uπ(j-α)	thermal resistance from	in free air	[1]	-	-	417	K/W
	junction to ambient		[2]	-	-	260	K/W

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.

#### 100 V, 1 A PNP low VCEsat transistor

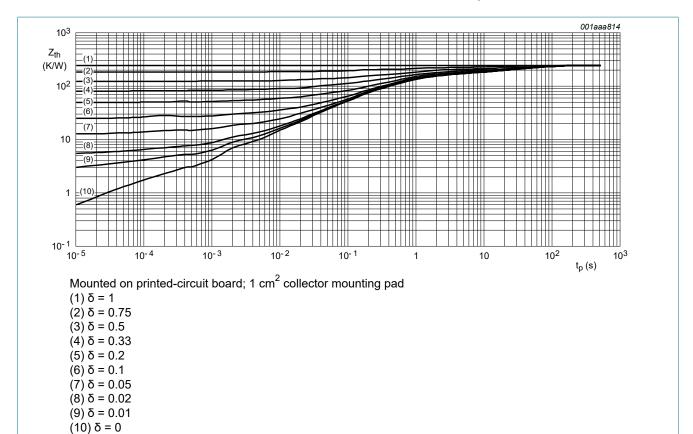
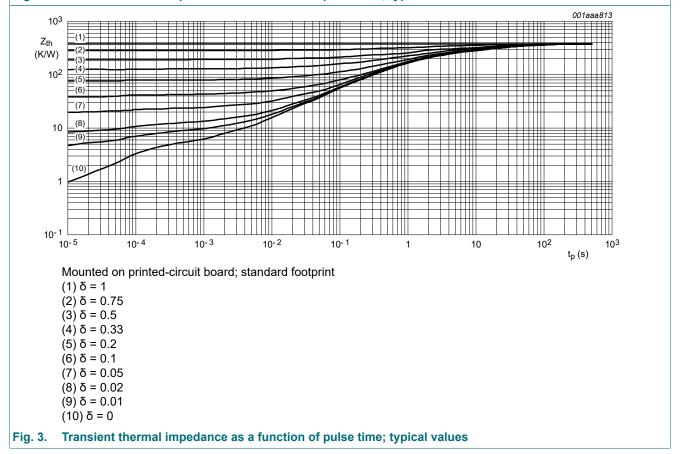


Fig. 2. Transient thermal impedance as a function of pulse time; typical values



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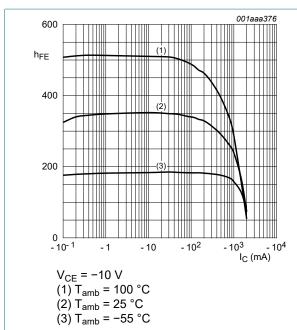
# 10. Characteristics

### **Table 7. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{(BR)CBO}$	collector-base breakdown voltage	$I_C = -100 \ \mu A; I_E = 0 \ A; T_{amb} = 25 \ ^{\circ}C$	-120	-	-	V
V <sub>(BR)CEO</sub>	collector-emitter breakdown voltage	$I_C = -10 \text{ mA}; I_B = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-100	-	-	V
V <sub>(BR)EBO</sub>	emitter-base breakdown voltage (collector open)	I <sub>E</sub> = -100 μA; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C	-5	-	-	V
I <sub>CBO</sub>	collector-base cut-off	V <sub>CB</sub> = -80 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	-100	nA
	current	V <sub>CB</sub> = -80 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C	-	-	-50	μΑ
I <sub>CES</sub>	collector-emitter cut-off current	V <sub>CE</sub> = -80 V; V <sub>BE</sub> = 0 V; T <sub>amb</sub> = 25 °C	-	-	-100	nA
I <sub>EBO</sub>	emitter-base cut-off current	V <sub>EB</sub> = -4 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	-100	nA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = -5 V; I <sub>C</sub> = -1 mA; T <sub>amb</sub> = 25 °C	150	-	-	
		V <sub>CE</sub> = -5 V; I <sub>C</sub> = -250 mA; T <sub>amb</sub> = 25 °C	150	-	-	
		$V_{CE}$ = -5 V; $I_{C}$ = -500 mA; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	150	-	450	
		$V_{CE}$ = -5 V; $I_{C}$ = -1 A; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	125	-	-	
V <sub>CEsat</sub>	collector-emitter	I <sub>C</sub> = -250 mA; I <sub>B</sub> = -25 mA; T <sub>amb</sub> = 25 °C	-	-	-120	mV
	saturation voltage	I <sub>C</sub> = -500 mA; I <sub>B</sub> = -50 mA; T <sub>amb</sub> = 25 °C	-	-	-180	mV
		$I_C$ = -1 A; $I_B$ = -100 mA; pulsed; $t_p \le$	-	-	-320	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	-	170	320	mΩ
V <sub>BEsat</sub>	base-emitter saturation voltage	I <sub>C</sub> = -1 A; I <sub>B</sub> = -100 mA; T <sub>amb</sub> = 25 °C	-	-	-1.1	V
$V_{BEon}$	base-emitter turn-on voltage	V <sub>CE</sub> = -5 V; I <sub>C</sub> = -1 A; T <sub>amb</sub> = 25 °C	-	-	-1	V
f <sub>T</sub>	transition frequency	$V_{CE}$ = -10 V; $I_{C}$ = -50 mA; f = 100 MHz; $T_{amb}$ = 25 °C	100	-	-	MHz
C <sub>c</sub>	collector capacitance	V <sub>CB</sub> = -10 V; I <sub>E</sub> = 0 A; i <sub>e</sub> = 0 A; f = 1 MHz; T <sub>amb</sub> = 25 °C	-	-	17	pF

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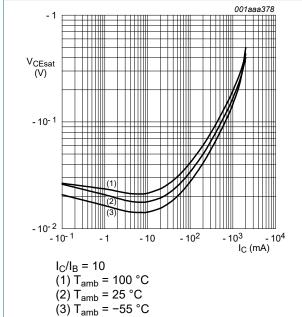
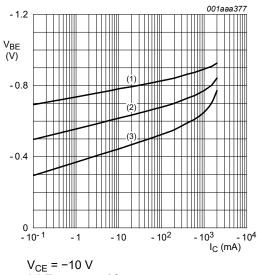
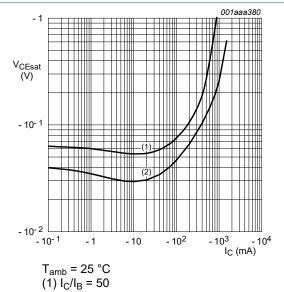


Fig. 6. Collector-emitter saturation voltage as a function of collector current; typical values



V<sub>CE</sub> = -10 V (1) T<sub>amb</sub> = -55 °C (2) T<sub>amb</sub> = 25 °C (3) T<sub>amb</sub> = 100 °C

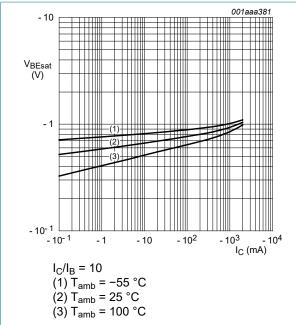
Fig. 5. Base-emitter voltage as a function of collector current; typical values



Collector-emitter saturation voltage as a Fig. 7. function of collector current; typical values

(2)  $I_C/I_B = 20$ 

#### 100 V, 1 A PNP low VCEsat transistor



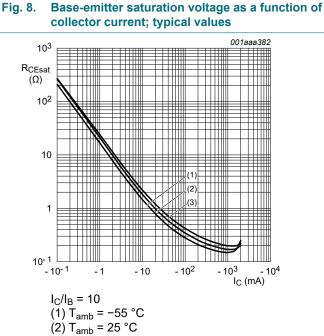


Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values

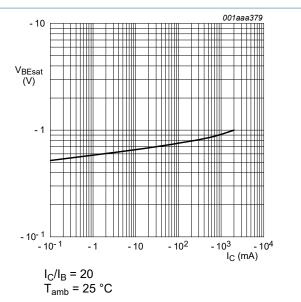


Fig. 9. Base-emitter saturation voltage as a function of collector current; typical values

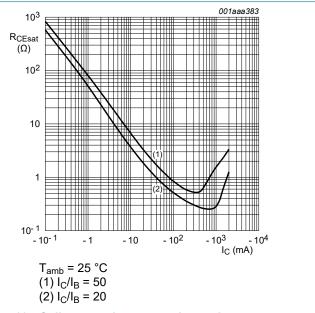


Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values

## 11. Test information

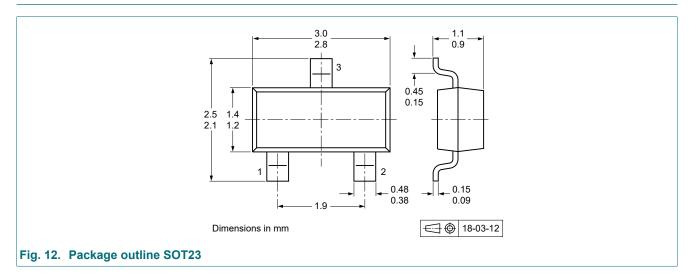
(3)  $T_{amb} = 100 \, ^{\circ}C$ 

## **Quality information**

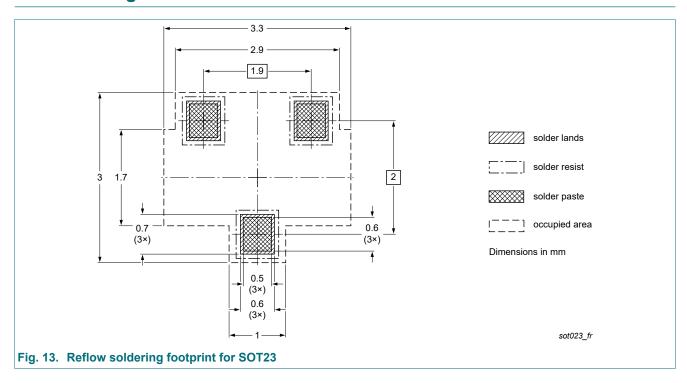
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

100 V, 1 A PNP low VCEsat transistor

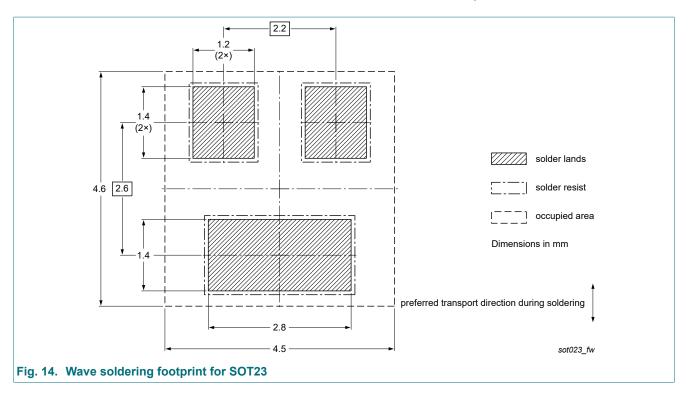
# 12. Package outline



## 13. Soldering



## 100 V, 1 A PNP low VCEsat transistor



100 V, 1 A PNP low VCEsat transistor

# 14. Revision history

## Table 8. Revision history

Data sheet ID	Release date		Change notice	Supersedes
PBSS9110T-Q v.1	20220519	Product data sheet	-	-

### 100 V, 1 A PNP low VCEsat transistor

## 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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